

Notice of References Cited	Application/Control No. 10/606,134		Applicant(s)/Patent Under Reexamination FRANCOM ET AL.	
	Examiner Elias Desta		Art Unit 2857	Page 1 of 1

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	B	US-2001/0054509	12-2001	Fujikami et al.	174/125.1
	C	US-6,028,440	02-2000	Roethig et al.	324/765
	D	US-6,741,086	05-2004	Maekawa et al.	324/754
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	L	US-			
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NON-PATENT DOCUMENTS

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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.